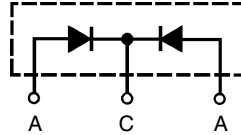


# Gallium Arsenide Schottky Rectifier

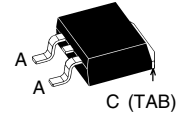
 $I_{FAV} = 2 \times 12 \text{ A}$   
 $V_{RRM} = 220/250 \text{ V}$   
 $C_{Junction} = 18 \text{ pF}$ 

Preliminary Data

$V_{RSM}$ V	$V_{RRM}$ V	Type
220	220	DGSK 20-022AS
250	250	DGSK 20-025AS



TO-263 AB



A = Anode, C = Cathode

Symbol	Conditions	Maximum Ratings	
$I_{FAV}$	$T_C = 25^\circ\text{C}$ ; DC	12	A
$I_{FAV}$	$T_C = 90^\circ\text{C}$ ; DC	9	A
$I_{FSM}$	$T_{VJ} = 45^\circ\text{C}$ ; $t_p = 10 \text{ ms}$ (50 Hz), sine	20	A
$T_{VJ}$		-55...+175	$^\circ\text{C}$
$T_{stg}$		-55...+150	$^\circ\text{C}$
$P_{tot}$	$T_C = 25^\circ\text{C}$	34	W

### Features

- Low forward voltage
- Very high switching speed
- Low junction capacity of GaAs
  - low reverse current peak at turn off
- Soft turn off
- Temperature independent switching behaviour
- High temperature operation capability
- Epoxy meets UL 94V-0

### Applications

- MHz Switched mode power supplies (SMPs)
- Small size SMPs
- High frequency converters
- Resonant converters

Symbol	Conditions	Characteristic Values		
		typ.	max.	
$I_R$ ①	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$		1.3	mA
	$T_{VJ} = 125^\circ\text{C}$ $V_R = V_{RRM}$	1.3		mA
$V_F$	$I_F = 5 \text{ A}$ ; $T_{VJ} = 125^\circ\text{C}$	1.3		V
	$I_F = 5 \text{ A}$ ; $T_{VJ} = 25^\circ\text{C}$	1.2	1.5	V
$C_J$	$V_R = 100 \text{ V}$ ; $T_{VJ} = 125^\circ\text{C}$	18		pF
$R_{thJC}$			4.4	K/W
Weight		2		g

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %  
 Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

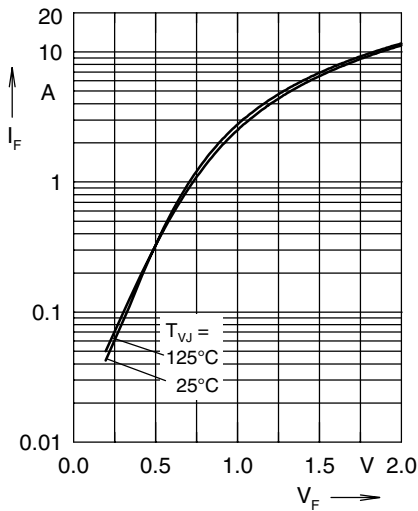


Fig. 1 typ. forward characteristics

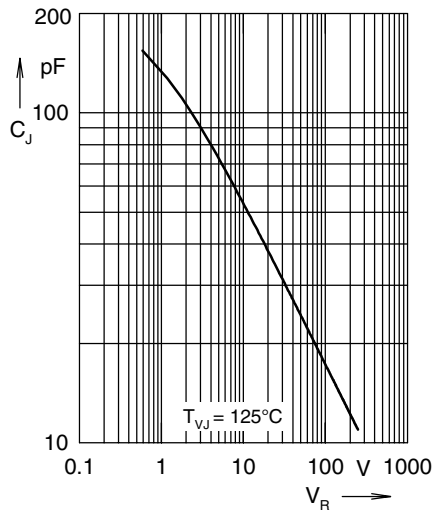


Fig. 2 typ. junction capacity versus blocking voltage

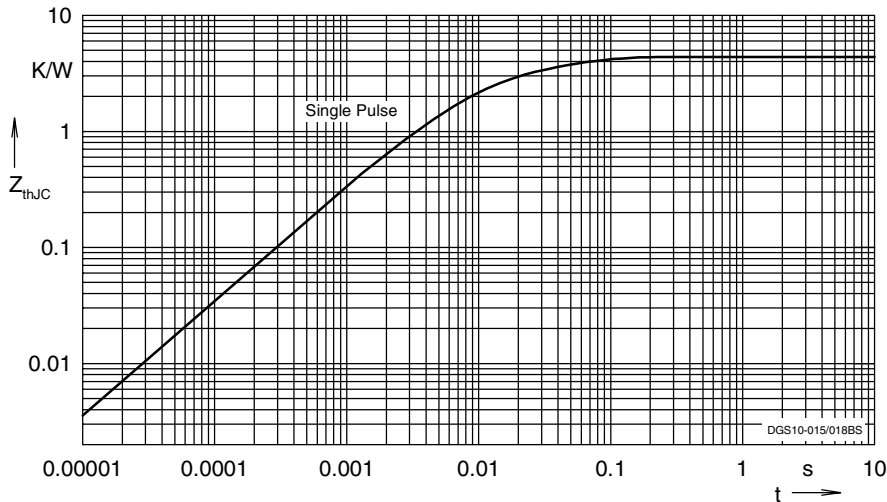


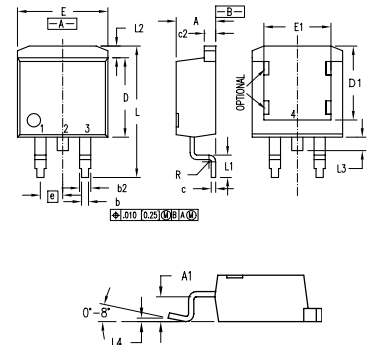
Fig. 3 typ. thermal impedance junction to case

Note:

explanatory comparison of the basic operational behaviour of rectifier diodes and Gallium Arsenide Schottky diodes:

	Rectifier Diode	GaAs Schottky Diode
conduction	by majority + minority carriers	by majority carriers only
forward characteristics	$V_F (I_F)$	$V_F (I_F)$ , see Fig. 1
turn off characteristics	extraction of excess carriers causes temperature dependant reverse recovery ( $t_{rr}$ , $I_{RM}$ , $Q_{rr}$ )	reverse current charges not temperature dependant
turn on characteristics	delayed saturation leads to $V_{FR}$	no turn on overvoltage peak

### Outline TO-263 AB



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	.160	.190
A1	2.03	2.79	.080	.110
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.46	0.74	.018	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	8.00	8.89	.315	.350
E	9.65	10.29	.380	.405
E1	6.22	8.13	.245	.320
e	2.54 BSC		.100 BSC	
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.20	0	.008
R	0.46	0.74	.018	.029